

Amendments to the Claims

Please enter the following amendments:

Amendments to the claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-34 (canceled).

Claims 35-37 (withdrawn).

Claim 38 (original): An integrated circuit including a first layer of material comprising silicon, a second layer of material comprising silicon, a first device, a second device, and a conductor, the conductor electrically connecting the first and second devices, at least a portion of the conductor being disposed between the first and second layers of material, the conductor including a first part, a second part, and a third part, the first and third parts comprising chromium, the second part comprising aluminum, the first part being disposed between the first layer of material and the second part, the third part being disposed between the second layer of material and the second part.

Claim 39 (original): An integrated circuit including a layer of material comprising silicon, a first device, a second device, and a conductor, the conductor electrically connecting the first and second devices, at least a portion of the conductor being disposed adjacent to the first layer of material, the conductor including a first part and a second part, the first part comprising chromium, the second part comprising aluminum, the first part being disposed between the layer of material and the second part.

Claim 40 (original): An integrated circuit including a multiplicity of devices and a network of conductors electrically connecting selective ones of the devices, the devices and the conductors being disposed in a material comprising silicon, each conductor in the network comprising aluminum and chromium.

Claims 41-46 (withdrawn).

Claim 47 (original): An integrated circuit including a first layer of material comprising silicon, a second layer of material comprising silicon, a first device, a second device, and a conductor, the conductor electrically connecting the first and second devices, at least a portion of the conductor being disposed between the first and second layers of material, the conductor including a first part, a second part, and a third part, the first and third parts comprising a first conductive material, the second part comprising a second conductive material, the first part being disposed between the first layer of material and the second part, the third part being disposed between the second layer of material and the second part.

48 (original): A circuit according to claim 47, wherein the first conductive material comprises chromium.

49 (original): A circuit according to claim 47, wherein the second conductive material comprises aluminum.

50 (original): A circuit according to claim 47, wherein the second conductive material comprises copper.

51 (original): An integrated circuit including a layer of material comprising silicon, a first device, a second device, and a conductor, the conductor electrically connecting the first and second devices, at least a portion of the conductor being disposed adjacent to the first layer of material, the conductor including a first part and a second part, the first part comprising a first conductive material, the second part comprising a second conductive material, the first part being disposed between the layer of material and the second part.

52 (original): A circuit according to claim 51, wherein the first conductive material comprises chromium.

53 (original): A circuit according to claim 51, wherein the second conductive material comprises aluminum.

54 (original): A circuit according to claim 51, wherein the second conductive material comprises copper.

55. (original): An integrated circuit including a multiplicity of devices and a network of conductors electrically connecting selective ones of the devices, the devices and the conductors being disposed in a material comprising silicon, each conductor in the network comprising a first conductive material and a second conductive material, the first conductive material preventing at least a portion of the second conductive material from contacting the material comprising silicon.

56 (original): A circuit according to claim 55, wherein the first conductive material comprises chromium.

57 (original): A circuit according to claim 55, wherein the second conductive material comprises aluminum.

58 (original): A circuit according to claim 55, wherein the second conductive material comprises copper.